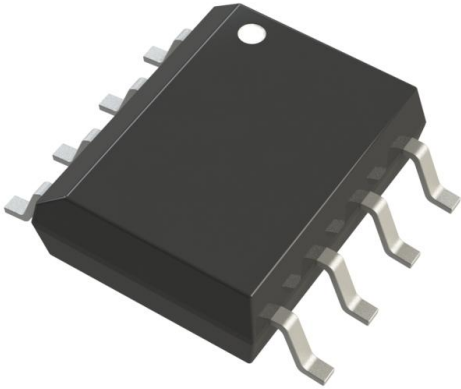


DMP3048LSD-13 Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	DMP3048LSD-13-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMP3048LSD-13
Description	MOSFET 2P-CH 30V 4.8A 8SO
Detailed Description	Mosfet Array 30V 4.8A (Ta) 1.7W Surface Mount 8-S OIC



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:

DMP3048LSD-13

Series:

-

Technology:

MOSFET (Metal Oxide)

FET Feature:

-

Current - Continuous Drain (Id) @ 25°C:

4.8A (Ta)

Vgs(th) (Max) @ Id:

1.3V @ 250µA

Input Capacitance (Ciss) (Max) @ Vds:

1438pF @ 15V

Operating Temperature:

-55°C ~ 150°C (Tj)

Package / Case:

8-SOIC (0.154", 3.90mm Width)

Base Product Number:

DMP3048

Manufacturer:

Diodes Incorporated

Product Status:

Active

Configuration:

2 P-Channel (Dual)

Drain to Source Voltage (Vdss):

30V

Rds On (Max) @ Id, Vgs:

48mOhm @ 5A, 10V

Gate Charge (Qg) (Max) @ Vgs:

13.5nC @ 4.5V

Power - Max:

1.7W

Mounting Type:

Surface Mount

Supplier Device Package:

8-SOIC

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMP3048LSD

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON) \text{ max}}$	I_D $T_A = +25^\circ\text{C}$
-30V	48mΩ @ $V_{GS} = -10V$	-4.8A
	57mΩ @ $V_{GS} = -4.5V$	-4.4A
	80mΩ @ $V_{GS} = -2.5V$	-3.7A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

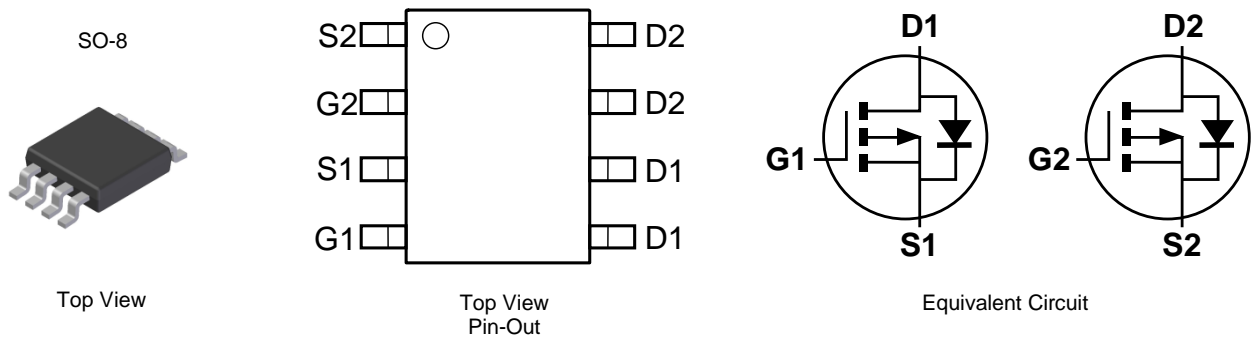
- DC-DC Converters
- Power Management Functions
- Backlighting

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.074 grams (Approximate)

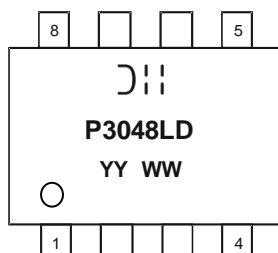


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3048LSD-13	SO-8	2500 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



⎓||| = Manufacturer's Marking
 P3048LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 16 = 2016)
 WW = Week (01 to 53)



DMP3048LSD

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-30	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	-4.8	A
Steady state T _A = +25°C		-3.8	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I _{DM}	-35	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-3.5	A
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	-19	A
Avalanche Energy (Note 7) L = 0.1mH	E _{AS}	19	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady state	102
		t < 10s	57
Total Power Dissipation (Note 6)	P _D	1.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady state	75
		t < 10s	40
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	18	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.5	—	-1.3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	28	48	mΩ	V _{GS} = -10V, I _D = -5A
		—	34	57		V _{GS} = -4.5V, I _D = -3.5A
		—	44	80		V _{GS} = -2.5V, I _D = -2.5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1438	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	92	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	76	—	pF	
Gate Resistance	R _g	—	11.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -10V)	Q _g	—	29.6	—	nC	V _{DS} = -20V, I _D = -5A
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	13.5	—	nC	
Gate-Source Charge	Q _{gs}	—	2.4	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	2.5	—	ns	V _{DS} = -15V, V _{GS} = -10V, R _L = 3Ω, R _G = 6Ω
Turn-On Rise Time	t _r	—	2.7	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	108	—	ns	
Turn-Off Fall Time	t _f	—	34	—	ns	
Reverse Recovery Time	t _{RR}	—	10	—	ns	
Reverse Recovery Charge	Q _{RR}	—	3.6	—	nC	I _F = -5.0A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



DMP3048LSD

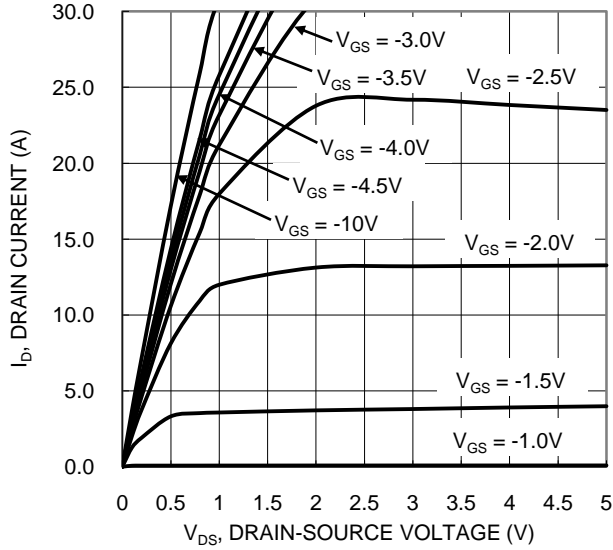


Figure 1. Typical Output Characteristic

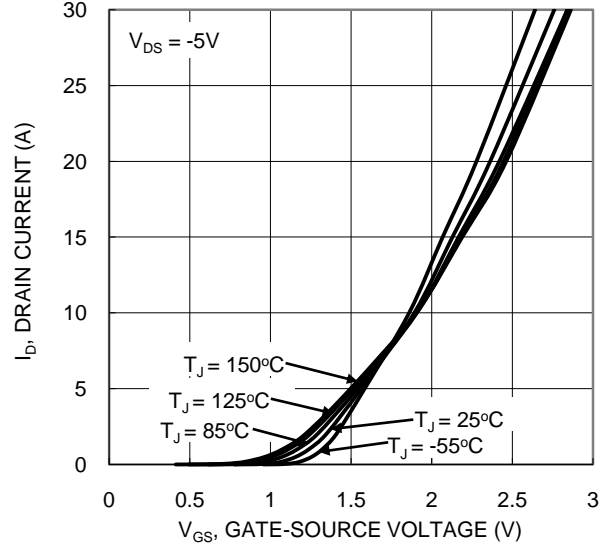


Figure 2. Typical Transfer Characteristic

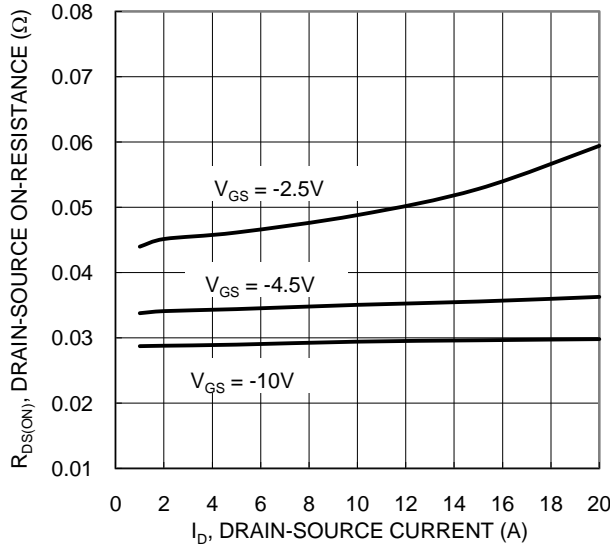


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

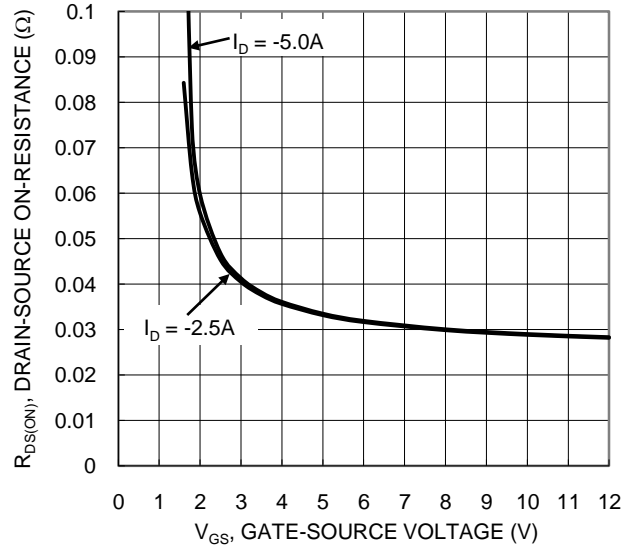


Figure 4. Typical Transfer Characteristic

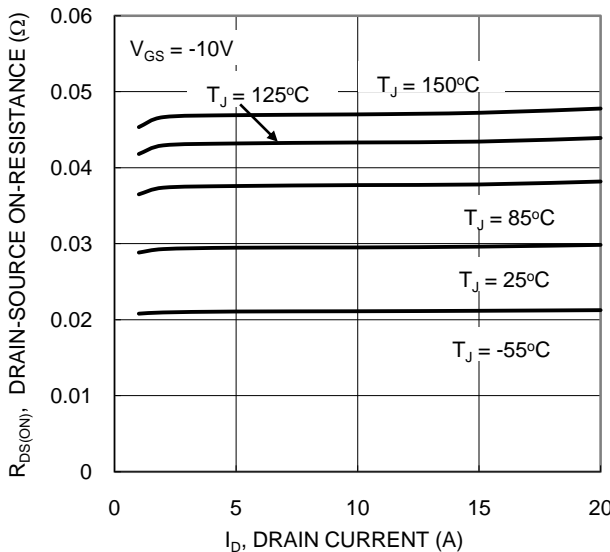


Figure 5. Typical On-Resistance vs Drain Current and Temperature

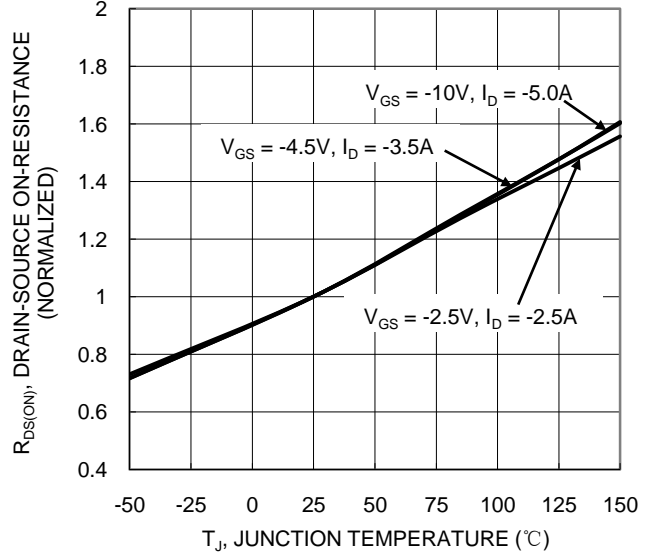


Figure 6. On-Resistance Variation with Temperature



DMP3048LSD

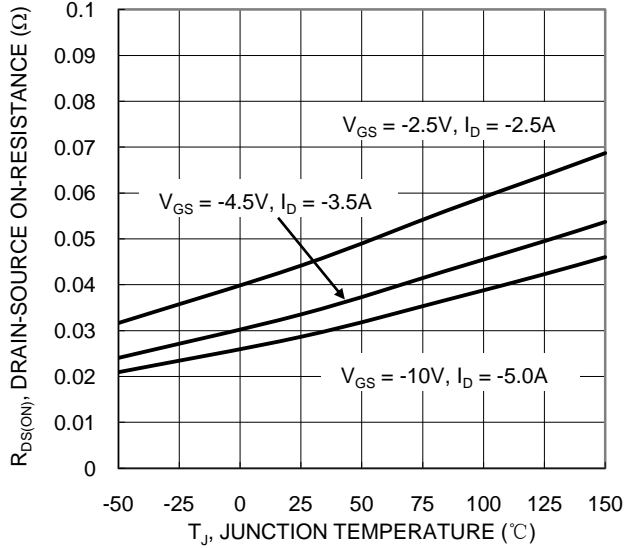


Figure 7. On-Resistance Variation with Temperature

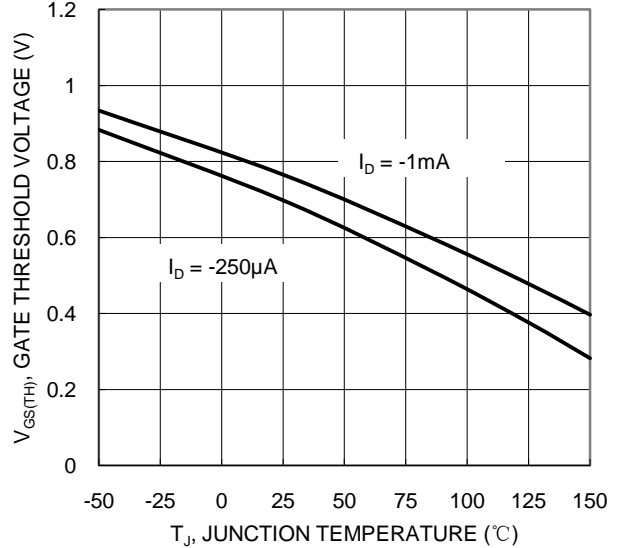


Figure 8. Gate Threshold Variation vs Junction Temperature

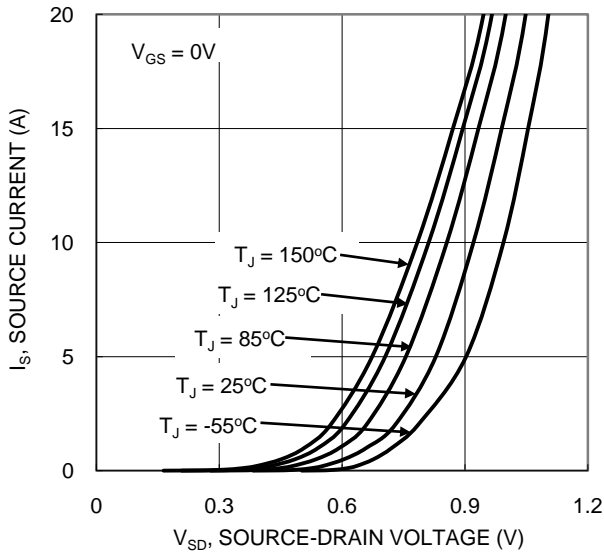


Figure 9. Diode Forward Voltage vs Current

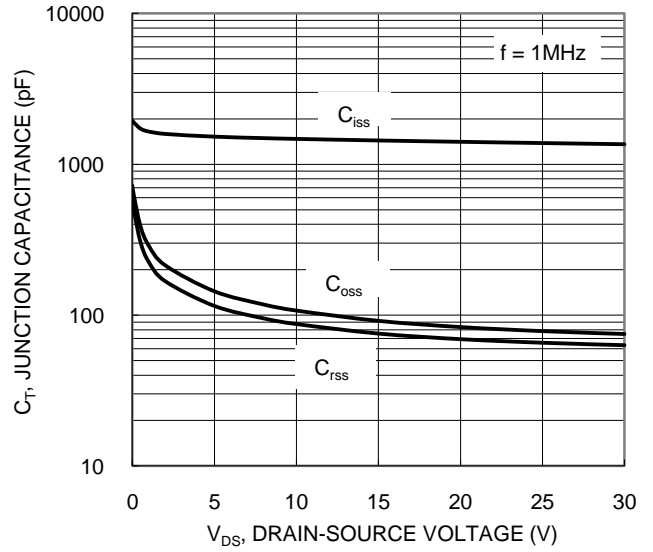


Figure 10. Typical Junction Capacitance

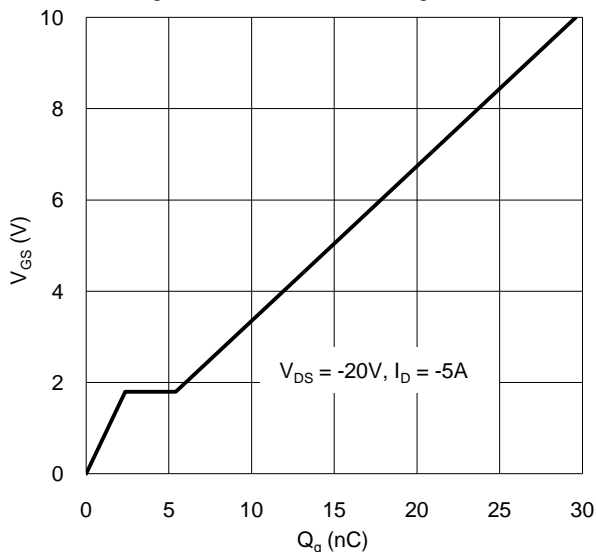


Figure 11. Gate Charge

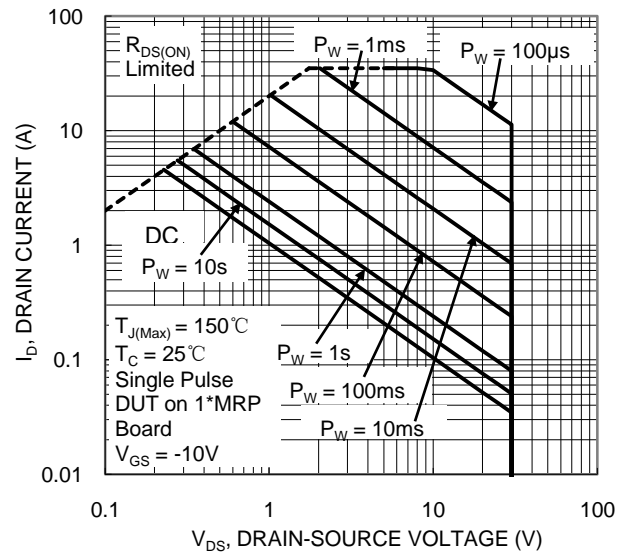


Figure 12. SOA, Safe Operation Area



DMP3048LSD

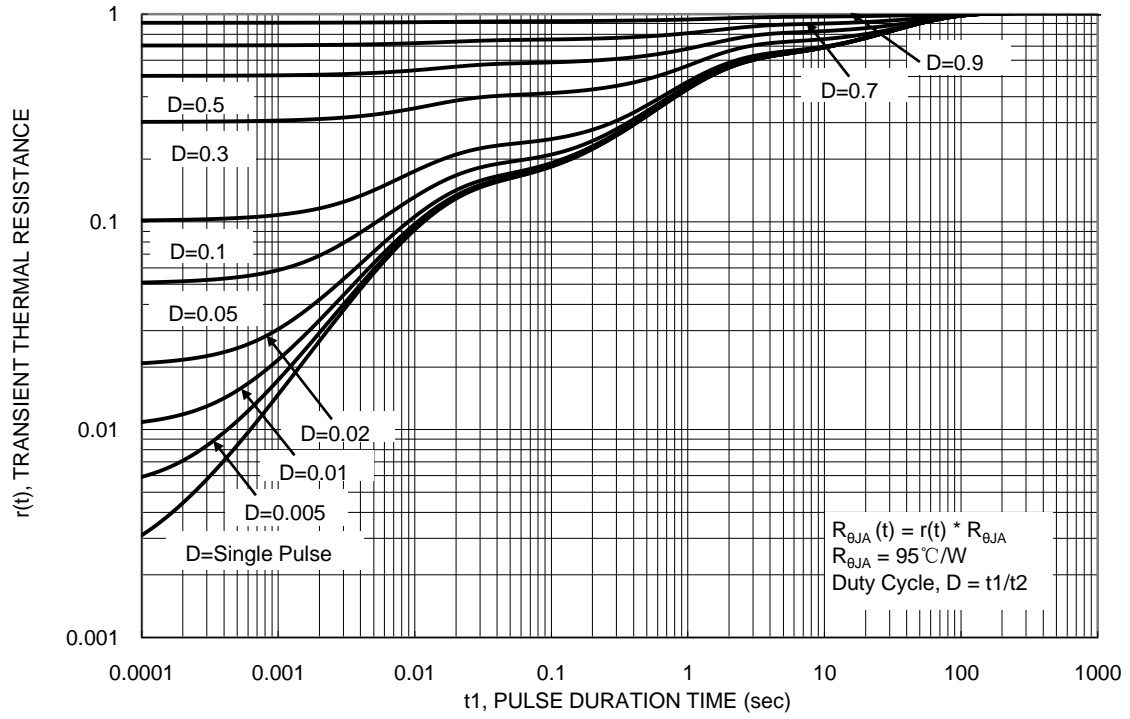


Figure 13. Transient Thermal Resistance

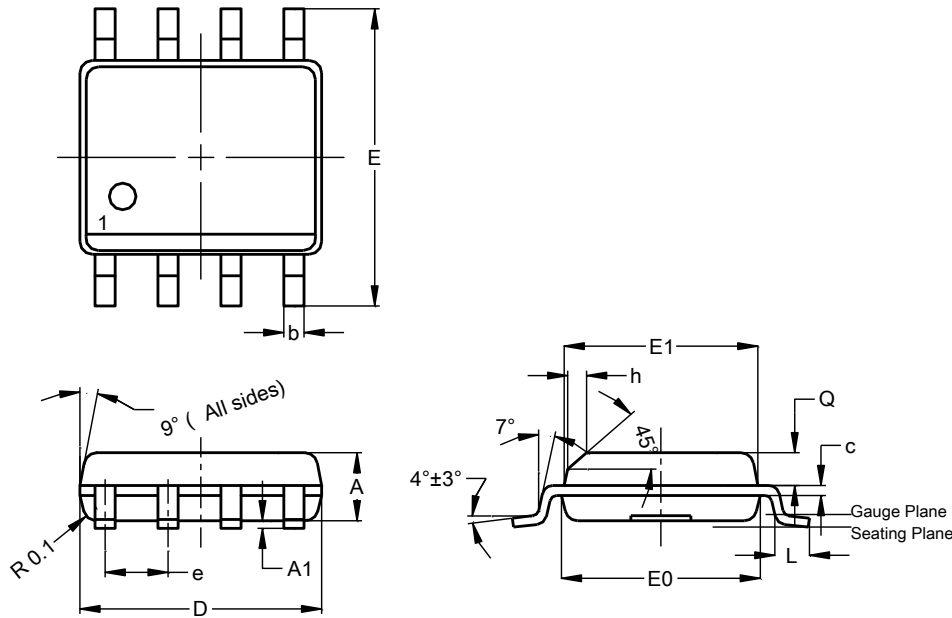


DMP3048LSD

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8

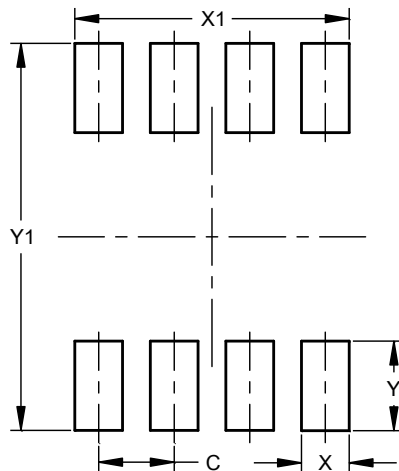


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SO-8



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50



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